

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

**Claims 1 – 13 (canceled)**

**Claim 14 (currently amended):** A process for forming a multilayer three-dimensional structure, comprising:

(a) forming a first layer comprising at least one structural material and at least one sacrificial material ~~of at least one material~~ on a substrate that may include one or more previously ~~deposited-formed~~ layers each formed from the at least one structural material and the at least one sacrificial ~~of one or more materials; and~~

(b) repeating the forming ~~operation of “(a)”~~ one or more times to form at least one subsequent layer on and adhered to the first layer or on and adhered to a previously formed subsequent layer ~~at least one previously formed layer~~ to build up a three-dimensional structure from a plurality of adhered layers;

wherein the forming of at least one layer of the plurality of adhered layers, comprises:

(1) ~~supplying a substrate on which one or more successive depositions of one or more materials may have occurred and will occur;~~

(12) supplying a mask that comprises at least one void and at least one surrounding protrusion of material;

(23) bringing the at least one protrusion of the mask into proximity to or into contact with the substrate or a selected previously formed layer so as to form at least one electrochemical process pocket having a desired registration with respect to any previous depositions and providing a desired electrolyte within the at least one electrochemical process pocket; and

(34) applying a desired electrical activation between at least one electrode, that may be part of the mask or separate therefrom, and the substrate or the selected previously formed layer, such that a desired modification of the substrate or previously formed layer occurs,

wherein the mask comprises at least two different materials where the material that is brought in proximity to or in contact with the substrate or the selected previously formed layer is less conformable than another material from which the mask is comprised.

**Claim 15 (original):** The process of claim 14 wherein the mask is an electrodeless mask.

**Claim 16 (original):** The process of claim 14 wherein the mask comprises an electrode that is used for deposition or etching.

**Claim 17 (currently amended):** The process of claim 14 wherein the desired modification comprises a selectively deposition of the at least one structural material or the at least one sacrificial -material.

**Claim 18 (currently amended):** The process of claim 17 additionally comprising a planarization of the selectively deposition of the at least one structural material or the at least one sacrificial deposited-material.

**Claim 19 (currently amended):** The process of ~~any of~~ claims 17, wherein the mask is used to selectively deposit material and an etching operation is performed after the deposition to reduce the presence of any unwanted depositions.

**Claim 20 (currently amended):** The process of claim 14 wherein the desired modification operates on the selected previously formed layer and where the desired modification comprises a selective etching of the at least one structural material or at least one sacrificial material which forms part of the selected previously formed layer material from the substrate.

**Claim 21 (original):** The process of claim 20 additionally comprising a planarization operation.

**Claim 22 (canceled).**